

METHOD FOR MAKING SEMICONDUCTOR DEVICE
INCLUDING BAND-ENGINEERED SUPERLATTICE

Abstract of the Disclosure

A method is for making a semiconductor device by forming a superlattice that, in turn, includes a plurality of stacked groups of layers. The method may also include forming regions for causing transport of charge carriers through the superlattice in a parallel direction relative to the stacked groups of layers. Each group of the superlattice may include a plurality of stacked base semiconductor monolayers defining a base semiconductor portion and an energy band-modifying layer thereon. The energy-band modifying layer may include at least one non-semiconductor monolayer constrained within a crystal lattice of adjacent base semiconductor portions so that the superlattice may have a higher charge carrier mobility in the parallel direction than would otherwise occur. The superlattice may also have a common energy band structure therein.